GENERAL DESCRIPTION

Glass passivated triacs in a full pack, plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

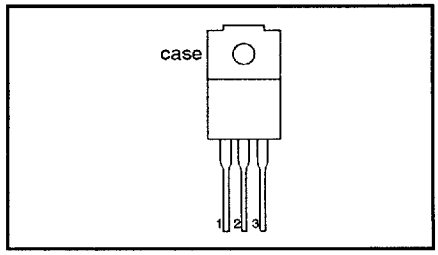
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT139F-	**500**	**600**	**800**	
	BT139F-	**500F**	**600F**	**800F**	
	BT139F-	**500G**	**600G**	**800G**	
V_{DRM}	Repetitive peak off-state voltages	500	600	800	V
$I_{T(RMS)}$	RMS on-state current	16	16	16	A
I_{TSM}	Non-repetitive peak on-state current	140	140	140	A

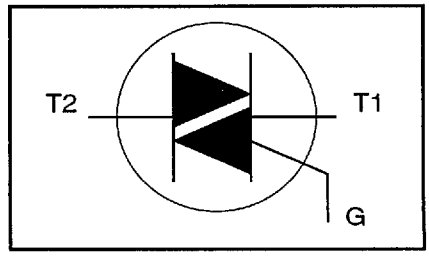
PINNING - SOT186

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500	**-600**	**-800**	
V_{DRM}	Repetitive peak off-state voltages		-	500[1]	600[1]	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{hs} \leq 38$ °C	-		16		A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 125$ °C prior to surge; with reapplied $V_{DRM(max)}$					
		t = 20 ms	-		140		A
		t = 16.7 ms	-		150		A
I^2t	I^2t for fusing	t = 10 ms	-		98		A^2s
dI_T/dt	Repetitive rate of rise of on-state current after triggering	I_{TM} = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs					
		T2+ G+	-		50		A/µs
		T2+ G-	-		50		A/µs
		T2- G-	-		50		A/µs
		T2- G+	-		10		A/µs
I_{GM}	Peak gate current		-		2		A
V_{GM}	Peak gate voltage		-		5		V
P_{GM}	Peak gate power		-		5		W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-		0.5		W
T_{stg}	Storage temperature		-40		150		°C
T_j	Operating junction temperature		-		125		°C

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

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ISOLATION LIMITING VALUE & CHARACTERISTIC

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65% ; clean and dustfree	-		1500	V
C_{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	12	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}hs}$	Thermal resistance junction to heatsink	full or half cycle				
		with heatsink compound	-	-	4.0	K/W
		without heatsink compound	-	-	5.5	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air	-	55	-	K/W

STATIC CHARACTERISTICS

T_j = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.			UNIT
		BT139F-			...	...F	...G	
I_{GT}	Gate trigger current	V_D = 12 V; I_T = 0.1 A						
		T2+ G+	-	5	35	25	50	mA
		T2+ G-	-	8	35	25	50	mA
		T2- G-	-	10	35	25	50	mA
		T2- G+	-	22	70	70	100	mA
I_L	Latching current	V_D = 12 V; I_{GT} = 0.1 A						
		T2+ G+	-	7	40	40	60	mA
		T2+ G-	-	20	60	60	90	mA
		T2- G-	-	8	40	40	60	mA
		T2- G+	-	10	60	60	90	mA
I_H	Holding current	V_D = 12 V; I_{GT} = 0.1 A	-	6	30	30	60	mA
V_T	On-state voltage	I_T = 20 A	-	1.2		1.6		V
V_{GT}	Gate trigger voltage	V_D = 12 V; I_T = 0.1 A	-	0.7		1.5		V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C	0.25	0.4		-		V
I_D	Off-state leakage current	V_D = $V_{DRM(max)}$; T_j = 125 °C	-	0.1		0.5		mA

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DYNAMIC CHARACTERISTICS

T_j = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.			TYP.	MAX.	UNIT
		BT139F-	...	...F	...G			
dV_D/dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 °C; exponential waveform; gate open circuit	100	50	200	250	-	V/µs
dV_{com}/dt	Critical rate of change of commutating voltage	V_{DM} = 400 V; T_j = 95 °C; $I_{T(RMS)}$ = 16 A; dI_{com}/dt = 7.2 A/ms; gate open circuit	-	-	10	20	-	V/µs
t_{gt}	Gate controlled turn-on time	I_{TM} = 20 A; V_D = $V_{DRM(max)}$; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	-	-	2	-	µs

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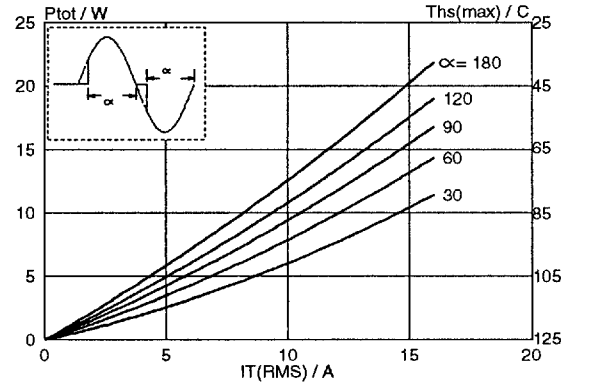

Fig.1. Maximum on-state dissipation, P_{tot}, versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

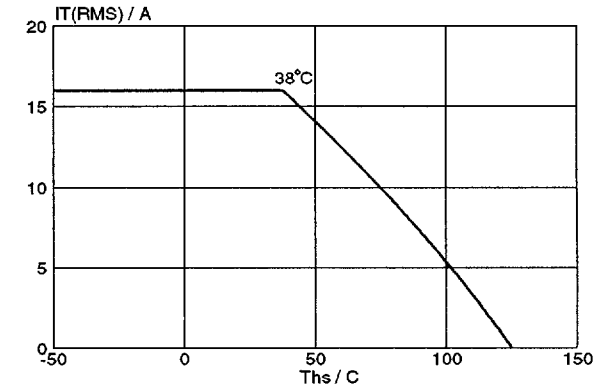

Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs}.

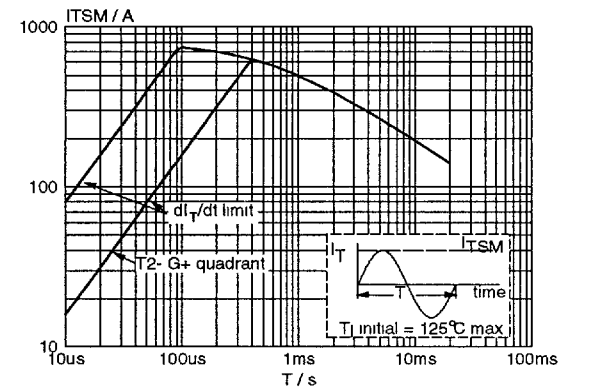

Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus pulse width t_p, for sinusoidal currents, $t_p \leq 20ms$.

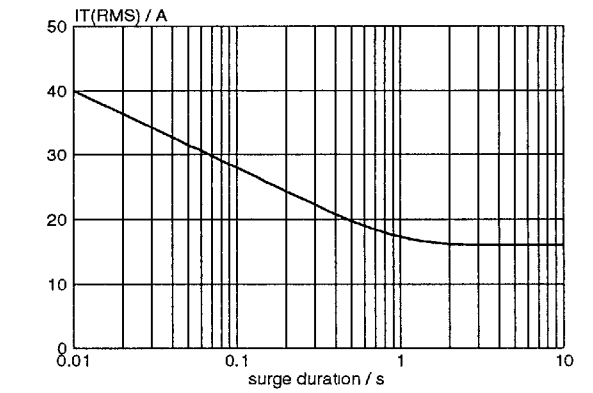

Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \leq 38°C$.

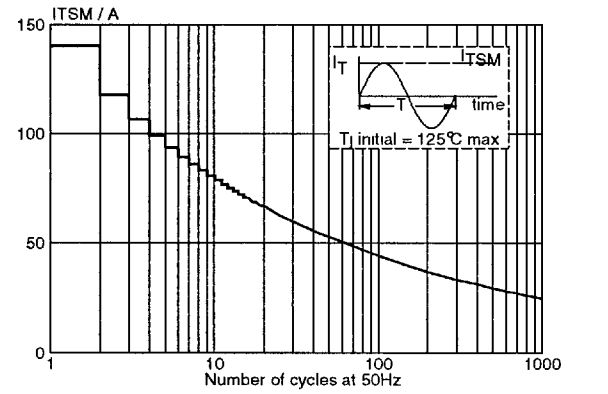

Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus number of cycles, for sinusoidal currents, f = 50 Hz.

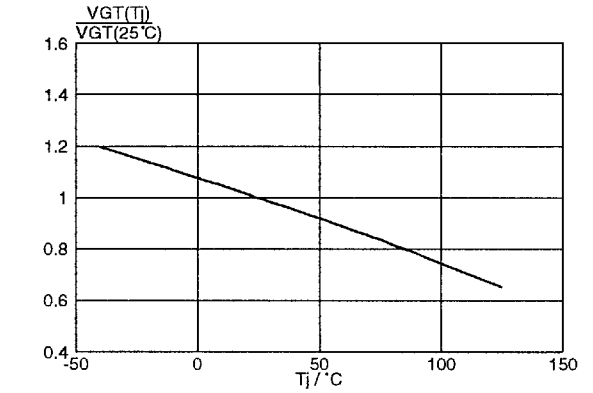

Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/ V_{GT}(25°C)$, versus junction temperature T_j.

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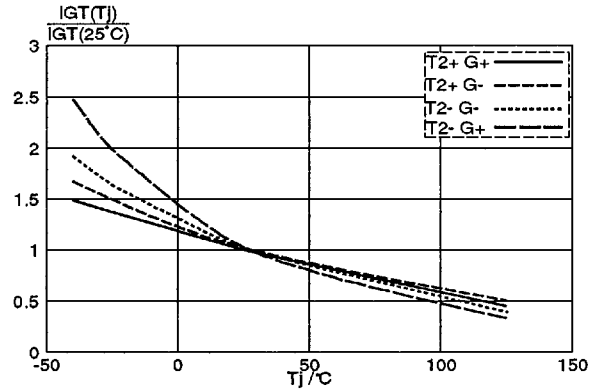

Fig.7. Normalised gate trigger current $I_{GT}(T_j)/ I_{GT}(25°C)$, versus junction temperature T_j.

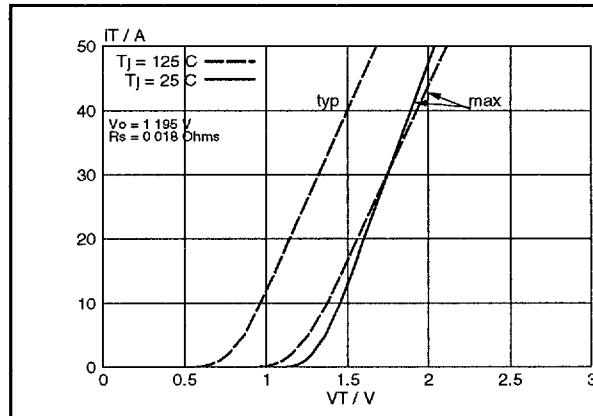

Fig.10. Typical and maximum on-state characteristic.

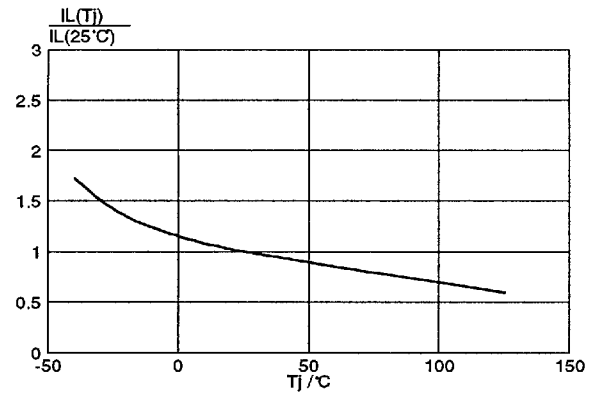

Fig.8. Normalised latching current $I_L(T_j)/ I_L(25°C)$, versus junction temperature T_j.

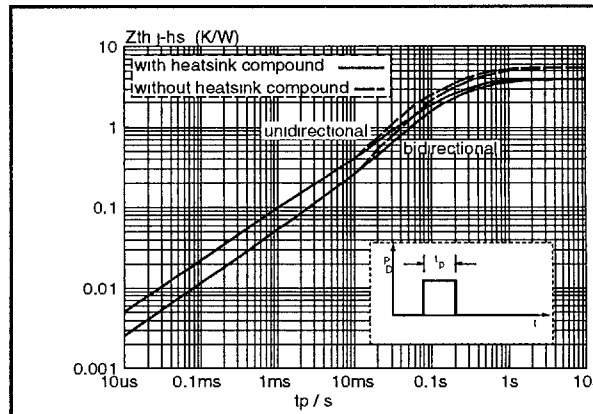

Fig.11. Transient thermal impedance $Z_{th\ j\text{-}hs}$, versus pulse width t_p.

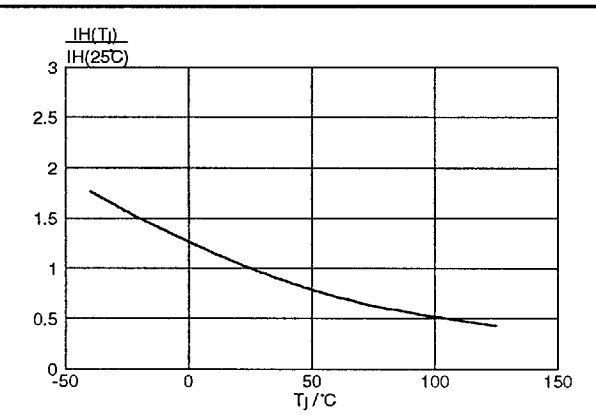

Fig.9. Normalised holding current $I_H(T_j)/ I_H(25°C)$, versus junction temperature T_j.

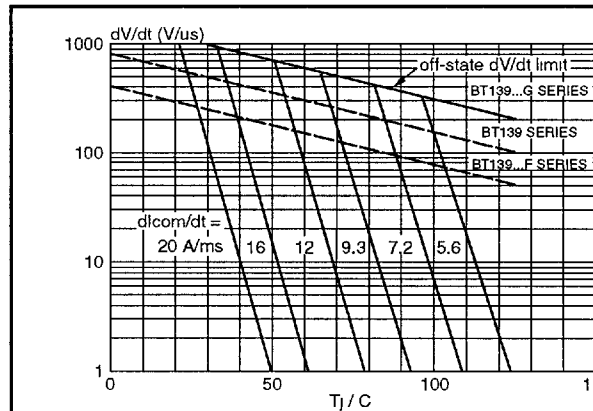

Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation dI_T/dt. The triac should commutate when the dV/dt is below the value on the appropriate curve for pre-commutation dI_T/dt.

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

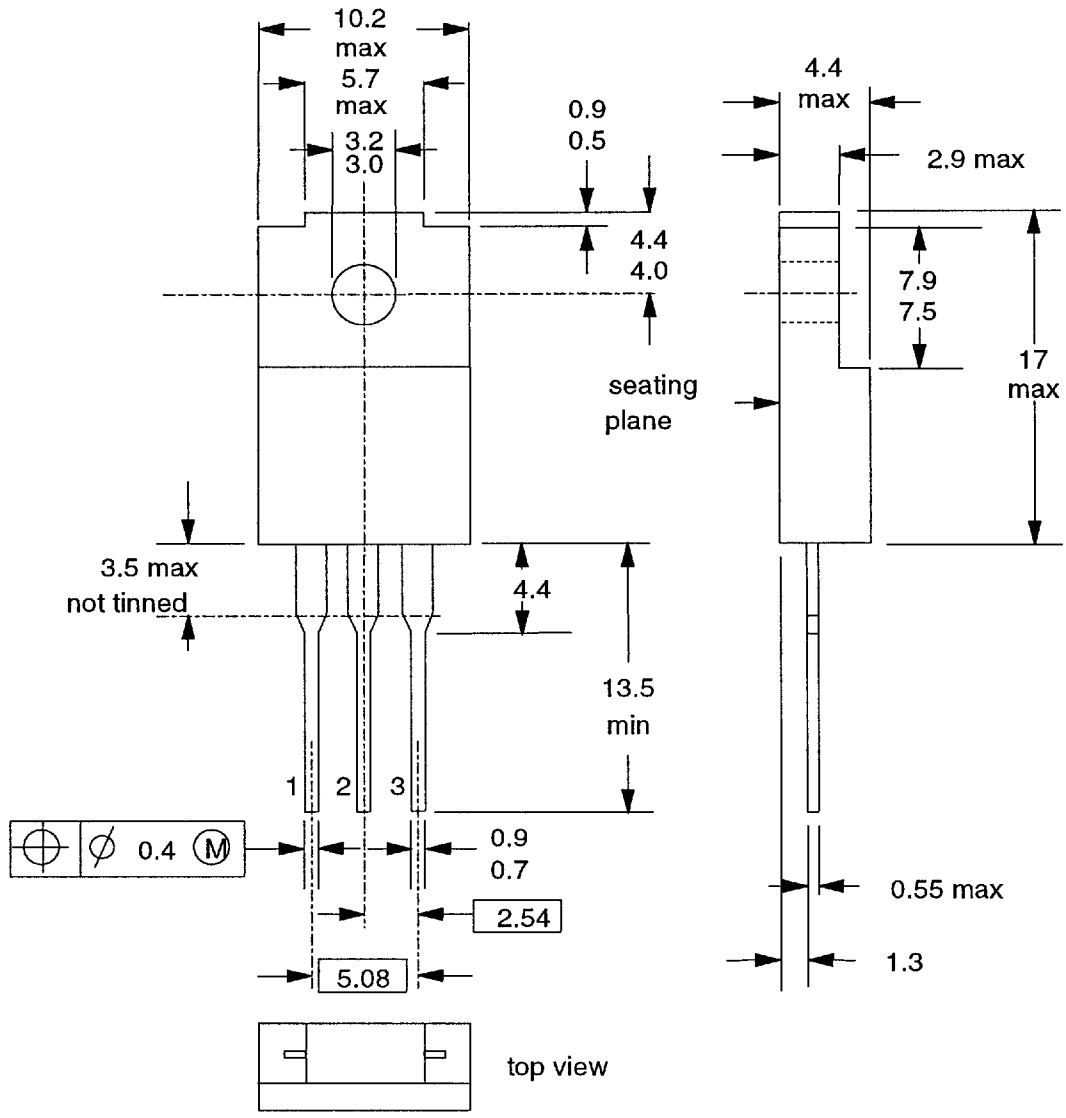

Fig.13. SOT186; The seating plane is electrically isolated from all terminals.

Notes

1. Accessories supplied on request: refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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